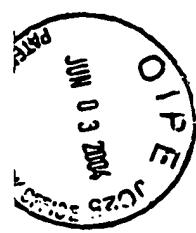


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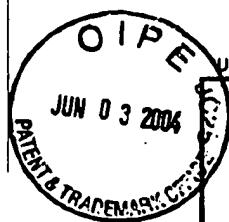
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Application Number	10/076,486
Filing Date	February 19, 2002
First Named Inventor	Stephen L. Casper
Art Unit	2818
Examiner Name	M. Tran

Attorney Docket Number M4065.0479/P479

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
		Number-Kind Code ² (if known)			Class	Sub
MT	AA	6,469,364	10/2002	Kozicki	257	529
	AB	2002/0168820 App.	11/2002	Kozicki		
	AC	2000/0072188 App	6/2002	Gilton		
	AD	2002/0123169 App	9/2002	Moore et al.		
	AE	2002/0123248 App.	9/2002	Moore et al.		
	AF	3,622,319	11/1971	Sharp	430	396
	AG	3,743,847	7/1973	Boland	250	505,1
	AH	4,269,935	5/1981	Masters et al.	430	323
	AI	4,312,938	1/1982	Drexler, et al.	430	496
MT	AJ	4,316,946	1/1982	Masters, et al.	430	9
	AK	4,320,191	3/1982	Yoshikawa et al.	430	296
	AL	4,405,710	9/1983	Balasubramanyam et al.	430	311
	AM	4,419,421	12/1983	Wichelhaus, et al.	429	323
	AN	4,795,657	1/1989	Formigoni et al.	427	96
	AO	4,847,674	7/1989	Sliwa et al.	257	767
	AP	4,499,557	2/1985	Holmberg et al.	365	163
	AQ	5,177,567	1/1993	Klersy et al.	257	4
	AR	5,219,788	6/1993	Abernathy et al.	438	636
	AS	5,238,862	8/1993	Blalock et al.	438	398
MT	AT	5,315,131	5/1994	Kishimoto et al.	257	57
	AU	5,350,484	9/1994	Gardner et al.	438	669
	AV	5,360,981	11/1994	Owen et al.	257	4
	AW	5,512,328	4/1996	Yoshimura et al.	438	498
	AX	5,512,773	4/1996	Wolf et al.	257	471
	AY	5,726,083	3/1998	Takaishi	438	210
	AA1	5,841,150	11/1998	Gonzalez et al.	257	3
	AB1	5,846,889	12/1998	Harbison et al.	501	40
	AC1	5,920,788	7/1999	Reinberg	438	466
MT	AD1	5,998,066	12/1999	Block et al.	430	5
	AE1	6,077,729	6/2000	Harshfield	438	128
	AF1	6,117,720	9/2000	Harshfield	438	238
	AG1	6,143,604	11/2000	Chiang et al.	438	253
	AH1	6,177,338	1/2001	Liaw et al.	438	629
	AI1	6,236,059	5/2001	Wolstenholme et al.	257	3
	AJ1	6,297,170	10/2001	Gabriel et al.	438	738
	AK1	6,300,684	10/2001	Gonzalez et al.	257	774
	AL1	6,316,784	11/2001	Zahorik et al.	257	3
	AM1	6,329,606	12/2001	Freyman et al.	174	260
MT	AN1	6,350,679	2/2002	McDaniel et al.	438	634
	AO1	6,376,284	4/2002	Gonzalez et al.	438	129
	AP1	6,391,688	5/2002	Gonzalez et al.	438	128
	AQ1	6,414,376	7/2002	Thakur et al.	257	640
	AR1	6,423,628	7/2002	Li et al.	438	622
	AS1	6,487,106	11/26/2002	Kozicki	365	153
MT	AT1	5,314,772	5/24/1994	Kozicki	430	14



Substitute for form 1449A/PTO				Complete If Known	
				Application Number	10/076,486
				Filing Date	February 19, 2002
				First Named Inventor	Stephen L. Casper
				Art Unit	2818
				Examiner Name	M. Tran
Sheet	2	of	4	Attorney Docket Number	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)					

MT	AU1	2002/0190350 APP	12/19/2002	Kozicki		
	AV1	2003/0027416 APP	2/6/2003	Moore		
	AW1	2003/0001229 APP	1/2/2003	Moore et al.		
	AX1	2002/0106849 APP	8/8/2002	Moore		
	AY1	2002/0127886 APP	9/12/2002	Moore et al.		
W	AZ1	2002/0123170 APP	9/5/2002	Moore et al.		
	BA1	2002/0163828 APP	11/2002	Krieger et al		
	BB1	6,072,716	6/2000	Jacobson et al.	365	163
	BC1	5,272,359	12/93	Nagasubramanian et al.	257	40
	BD1	4,671,618	6/87	Wu et al.	349	92
	BE1	4,800,526	1/89	Lewis	365	118
W	BF1	2003/0035314	02/20/03	Kozicki		
	BG1	2003/0035315	02/20/03	Kozicki		
	BH1	6,314,014	11/6/01	Lowrey et al.	365	100
	BI1	5,883,827	3/16/99	Morgan	365	100
MT	BJ1	4,112,512	9/5/78	Arzubi et al.	365	149

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Application Number	10/076,486
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First Named Inventor	Stephen L. Casper
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Examiner Name	M. Tran
Attorney Docket Number	M4065.0479/P479

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ²
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
BLT	BA	JP 56126916	10/1981	Akira et al.		
	BB					

Examiner Signature

M. TRAN

Date Considered

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Application Number	10/076,486
Filing Date	February 19, 2002
First Named Inventor	Stephen L. Casper et al.
Group Art Unit	2818
Examiner Name	M. Tran
Attorney Docket Number	M4065.0479/P479

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

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Substitute for form 1449A/B/PTO				Complete if Known	
				Application Number	10/076,486
				Filing Date	February 19, 2002
				First Named Inventor	Stephen L. Casper
				Art Unit	2818
				Examiner Name	M. Tran
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U.S. PATENT DOCUMENTS					
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MLY	A	US 2004/0035401	2/2004	Ramachandran et al.	clas
	B	US 2003/0212724	11/2003	Ovshinsky et al.	
	C	US 2003/0048744	3/2003	Ovshinsky et al.	
	D	US 2003/0212725	11/2003	Ovshinsky et al.	
	E	US RE 37,259E	7/2001	Ovshinsky	
	F	US 3,271,591	9/1966	Ovshinsky	327 500
	G	US 3,961,314	6/1976	Klose et al.	365 113
	H	US 3,966,317	6/1976	Wacks et al.	355 19
	I	US 3,983,542	11/1976	Ovshinsky	365 113
	J	US 3,988,720	10/1976	Ovshinsky	365 113
MLY	K	US 4,177,474	12/1979	Ovshinsky	252 62
	L	US 4,267,261	5/1981	Hallman et al.	420 322
	M	US 4,597,162	7/1986	Johnson et al.	428 16
	N	US 4,608,296	8/1986	Keem et al.	428 215
	O	US 4,637,895	1/1987	Ovshinsky et al.	252 372
	P	US 4,646,266	2/1987	Ovshinsky et al.	365 105
	Q	US 4,664,939	5/1987	Ovshinsky	438 62
	R	US 4,668,968	5/1987	Ovshinsky et al.	257 61
	S	US 4,670,763	6/1987	Ovshinsky et al.	257 57
	T	US 4,673,957	6/1987	Ovshinsky et al.	257 58
MLY	U	US 4,678,679	7/1987	Ovshinsky	427 562
	V	US 4,696,758	9/1987	Ovshinsky et al.	252 501.1
	W	US 4,698,234	10/1987	Ovshinsky et al.	438 62
	X	US 4,710,899	12/1987	Young et al.	365 113
	Y	US 4,728,406	3/1988	Banerjee et al.	204 192,29
	Z	US 4,737,379	4/1988	Hudgens et al.	427 575
	A1	US 4,766,471	8/1988	Ovshinsky et al.	257 53
	B1	US 4,769,338	9/1988	Ovshinsky et al.	438 151
	C1	US 4,775,425	10/1988	Guha et al.	136 249
	D1	US 4,788,594	11/1988	Ovshinsky et al.	348 64
	E1	US 4,809,044	2/1989	Pryor et al.	257 3
	F1	US 4,818,717	4/1989	Johnson et al.	438 130
MLY	G1	US 4,843,443	6/1989	Ovshinsky et al.	257 59
	H1	US 4,845,533	7/1989	Pryor et al.	257 4
	I1	US 4,853,785	8/1989	Ovshinsky et al.	348 302
	J1	US 4,891,330	1/1990	Guha et al.	438 488
	K1	US 5,128,099	7/1992	Strand et al.	420 579
	L1	US 5,159,661	10/1992	Ovshinsky et al.	706 33
	M1	US 5,166,758	11/1992	Ovshinsky et al.	257 3
	N1	US 5,177,567	1/1993	Klersy et al.	257 4
	O1	US 5,296,716	3/1994	Ovshinsky et al.	257 3
	P1	US 5,335,219	8/1994	Ovshinsky et al.	365 288
	Q1	US 5,359,205	10/1994	Ovshinsky	257 3
	R1	US 5,341,328	8/1994	Ovshinsky et al.	365 113
	S1	US 5,406,509	4/1995	Ovshinsky et al.	265 113



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Application Number	10/076,486
Filing Date	February 19, 2002
First Named Inventor	Stephen L. Casper
Art Unit	2818
Examiner Name	M. Tran

Attorney Docket Number M4065.0479/P479

Clos Sub

1A	T1	US 5,414,271	5/1995	Ovshinsky et al.	257	3
	U1	US 5,534,711	7/1996	Ovshinsky et al.	257	3
	V1	US 5,534,712	7/1996	Ovshinsky et al.	257	3
	W1	US 5,536,947	7/1996	Klersy et al.	257	3
	X1	US 5,543,737	8/1996	Ovshinsky	326	104
	Y1	US 5,591,501	1/1997	Ovshinsky et al.	420	64.1
	Z1	US 5,596,522	1/1997	Ovshinsky et al.	365	113
1A	A2	US 5,687,112	11/1997	Ovshinsky	365	163
	B2	US 5,694,054	12/1997	Ovshinsky et al.	326	35
	C2	US 5,714,768	2/1998	Ovshinsky et al.	257	40
	D2	US 5,825,046	10/1998	Czubatyj et al.	257	2
	E2	US 5,912,839	6/1999	Ovshinsky et al.	365	185,03
	F2	US 5,933,365	8/1999	Klersy et al.	365	148
	G2	US 6,011,757	1/2000	Ovshinsky	369	13,75
	H2	US 6,087,674	7/2000	Ovshinsky et al.	257	2
	I2	US 6,141,241	10/2000	Ovshinsky et al.	365	163
	J2	US 6,339,544	1/2002	Chiang et al.	365	163
1A	K2	US 6,404,665	6/2002	Lowery et al.	365	100
	L2	US 6,429,064	8/2002	Wicker	438	238
	M2	US 6,437,383	8/2002	Xu	257	300
	N2	US 6,462,984	10/2002	Xu et al.	365	175
	O2	US 6,480,438	11/2002	Park	365	230,06
	P2	US 6,487,113	11/2002	Park et al.	365	163
	Q2	US 6,501,111	12/2002	Lowery	257	295
	R2	US 6,507,061	1/2003	Hudgens et al.	257	4
	S2	US 6,511,862	1/2003	Hudgens et al.	438	95
	T2	US 6,511,867	1/2003	Lowery et al.	438	128
	U2	US 6,512,241	1/2003	Lai	257	4
1A	V2	US 6,514,805	2/2003	Xu et al.	438	164
	W2	US 6,531,373	3/2003	Gill et al.	438	400
	X2	US 6,534,781	3/2003	Dennison	257	5
	Y2	US 6,545,287	4/2003	Chiang	257	3
	Z2	US 6,545,907	4/2003	Lowery et al.	365	163
	A3	US 6,555,860	4/2003	Lowery et al.	257	296
	B3	US 6,563,164	5/2003	Lowery et al.	257	314
	C3	US 6,566,700	5/2003	Xu	257	296
	D3	US 6,567,293	5/2003	Lowery et al.	365	100
	E3	US 6,569,705	5/2003	Chiang et al.	438	95
1A	F3	US 6,570,784	5/2003	Lowery	365	163
	G3	US 6,576,921	6/2003	Lowery	257	42
	H3	US 6,586,761	7/2003	Lowery	257	3
	I3	US 6,589,714	7/2003	Maimon et al.	438	313
	J3	US 6,590,807	7/2003	Lowery	365	175
	K3	US 6,593,176	7/2003	Dennison	438	200
	L3	US 6,597,009	7/2003	Wicker	257	4
	M3	US 6,605,527	8/2003	Dennison et al.	438	618
	N3	US 6,613,604	9/2003	Maimon et al.	438	95
	O3	US 6,621,095	9/2003	Chiang et al.	257	5
1A	P3	US 6,625,054	9/2003	Lowery et al.	365	148
	Q3	US 6,642,102	11/2003	Xu	438	257



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Sheet	3	of	3	Attorney Docket Number	M4065.0479/P479
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MR	R3	US 6,646,297	11/2003	Dennison	257	296
	S3	US 6,649,928	11/2003	Dennison	257	4
	T3	US 6,667,900	12/2003	Lowery et al.	365	171
	U3	US 6,671,710	12/2003	Ovshinsky et al.	708	493
	V3	US 6,673,700	1/2004	Dennison et al.	438	466
	W3	US 6,674,115	1/2004	Hudgens et al.	257	310
	X3	US 6,687,427	2/2004	Ramalingam et al.	365	163
	Y3	US 6,690,026	2/2004	Peterson	385	16
	Z3	US 6,696,355	2/2004	Dennison	257	4
MR	A4	US 6,687,153	2/2004	Lowery	436	597
	B4	US 6,707,712	3/2004	Lowery	365	173
	C4	US 6,714,954	3/2004	Ovshinsky et al.	708	200

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Examiner Initials*	Cite No. ¹	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ²
		Country Code ³	Number ⁴ -Kind Code ⁵ (if known)				

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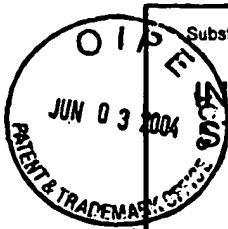
NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²

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Attorney Docket Number

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Application Number	10/076,486
Filing Date	February 19, 2002
First Named Inventor	Stephen L. Casper
Art Unit	2818
Examiner Name	Not Known
Attorney Docket Number	M4065.0479/P479

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Subclauses/FIGURES Appear	
		Number-Kind Code ² (if known)			clas	Subcl
WT	AA	6,388,324	05/14/2002	Kozicki et al.	257	750
WT	AB	US 2002/0000666	01/03/2002	Kozicki et al.	A	
	AC	5,500,532	03/19/1996	Kozicki et al.	250	372
	AD	6,418,049	07/09/2002	Kozicki et al.	365	174
	AE	5,751,012	05/12/1998	Wolstenholme et al.	257	5
	AF	5,789,277	08/04/1998	Zahorik et al.	438	130
WT	AG	6,348,365	02/19/2202	Moore et al.	438	130

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		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
MJ	BA	WO 02/21542	03/14/2002	Kozicki et al.		
J	BB	WO 00/48196	08/17/2000	Kozicki et al.		
MJ	BC	WO 97/48032	12/18/1997	Kozicki et al.		
MJ	BD	WO 99/28914	06/10/1999	Kozicki et al.		

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First Named Inventor	Stephen L. Casper
Group Art Unit	2818
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Attorney Docket Number M4065.0479/P479

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

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KJ	CA	Abdel-Ali, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge5As38Te57 chalcogenide glass, Vacuum 59 (2000) 845-853.	
	CB	Adler, D.; Moss, S.C., Amorphous memories and bistable switches, J. Vac. Sci. Technol. 9 (1972) 1182-1189.	
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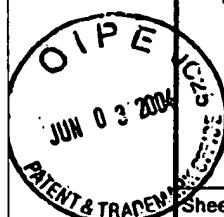
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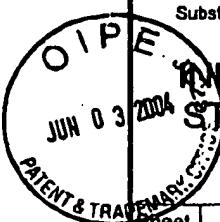
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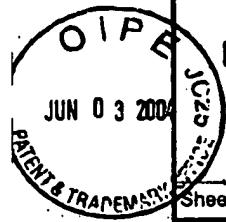
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